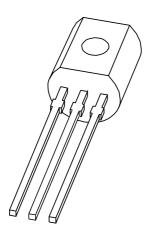
DISCRETE SEMICONDUCTORS

DATA SHEET



MPSA92 PNP high-voltage transistor

Product data sheet Supersedes data of 2001 Dec 07 2004 Aug 20



PNP high-voltage transistor

MPSA92

FEATURES

• Low current (max. 100 mA)

• High voltage (max. 300 V).

APPLICATIONS

• General purpose switching and amplification.

DESCRIPTION

PNP high-voltage transistor in a TO-92; SOT54 plastic package. NPN complement: MPSA42.

PINNING

PIN	DESCRIPTION
1	collector
2	base
3	emitter

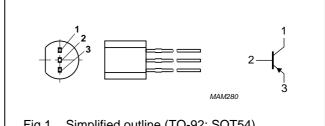


Fig.1 Simplified outline (TO-92; SOT54) and symbol.

LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V _{CBO}	collector-base voltage	open emitter	_	-300	V
V _{CEO}	collector-emitter voltage	open base	_	-300	V
V _{EBO}	emitter-base voltage	open collector	_	-5	V
I _C	collector current (DC)		_	-100	mA
I _{CM}	peak collector current		_	-200	mA
I _{BM}	peak base current		_	-100	mA
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C	_	625	mW
T _{stg}	storage temperature		-65	+150	°C
Tj	junction temperature		_	150	°C
T _{amb}	operating ambient temperature		-65	+150	°C

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THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
R _{th j-a}	thermal resistance from junction to ambient	note 1	200	K/W

Note

1. Transistor mounted on an FR4 printed-circuit board.

CHARACTERISTICS

 $T_j = 25$ °C unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
I _{CBO}	collector cut-off current	I _E = 0; V _{CB} = -200 V	-	-250	nA
I _{EBO}	emitter cut-off current	$I_C = 0; V_{BE} = -3 \text{ V}$	_	-100	nA
h _{FE}	DC current gain	V _{CE} = -10 V; note 1			
		$I_C = -1 \text{ mA}$	25	_	
		$I_{\rm C} = -10 \; {\rm mA}$	40	_	
		$I_C = -30 \text{ mA}$	25	_	
V _{CEsat}	collector-emitter saturation voltage	$I_C = -20 \text{ mA}$; $I_B = -2 \text{ mA}$; note 1	_	-500	mV
V _{BEsat}	base-emitter saturation voltage	$I_C = -20 \text{ mA}$; $I_B = -2 \text{ mA}$; note 1	_	-900	mV
C _c	collector capacitance	$I_E = i_e = 0$; $V_{CB} = -20 \text{ V}$; $f = 1 \text{ MHz}$	_	6	pF
f _T	transition frequency	$I_C = -10 \text{ mA}; V_{CE} = -20 \text{ V};$ f = 100 MHz	50	_	MHz

Note

1. Pulse test: $t_p \le 300~\mu s;~\delta \le 0.02.$

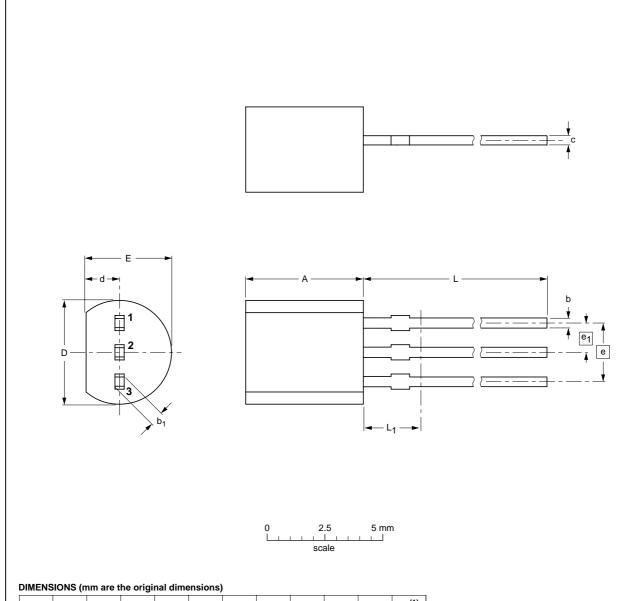
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PACKAGE OUTLINE

Plastic single-ended leaded (through hole) package; 3 leads

SOT54



UNIT	Α	b	b ₁	С	D	d	E	е	e ₁	L	L ₁ ⁽¹⁾ max.	
mm	5.2 5.0	0.48 0.40	0.66 0.55	0.45 0.38	4.8 4.4	1.7 1.4	4.2 3.6	2.54	1.27	14.5 12.7	2.5	

Note

1. Terminal dimensions within this zone are uncontrolled to allow for flow of plastic and terminal irregularities.

OUTLINE		REFER	EUROPEAN	ISSUE DATE			
VERSION	SION IEC JEDEC		JEITA	JEITA		ISSUE DATE	
SOT54		TO-92	SC-43A			-04-06-28 04-11-16	

PNP high-voltage transistor

MPSA92

DATA SHEET STATUS

DOCUMENT STATUS ⁽¹⁾	PRODUCT STATUS ⁽²⁾	DEFINITION
Objective data sheet	Development	This document contains data from the objective specification for product development.
Preliminary data sheet	Qualification	This document contains data from the preliminary specification.
Product data sheet	Production	This document contains the product specification.

Notes

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Customer notification

This data sheet was changed to reflect the new company name NXP Semiconductors, including new legal definitions and disclaimers. No changes were made to the technical content, except for package outline drawings which were updated to the latest version.

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